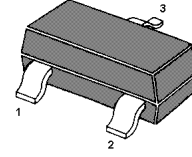
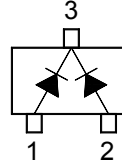


BAV74

Silicon Epitaxial Planar Switching Diode

Applications

- Ultra high speed switching application



Marking Code: **A4**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	60	V
Continuous Reverse Voltage	V_R	50	V
Forward Current (DC)	I_{FSM}	215	mA
Single Diode Loaded		125	
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
at $t = 1\text{ s}$		1	
at $t = 1\text{ ms}$		4	
Power Dissipation	P_d	350	mW
Operating Junction Temperature Range	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage	V_F	715	mV
at $I_F = 1\text{ mA}$		855	mV
at $I_F = 10\text{ mA}$		1	V
at $I_F = 150\text{ mA}$		1.25	V
Reverse Current	I_R	30	nA
at $V_R = 25\text{ V}$		0.1	μA
at $V_R = 50\text{ V}$		30	μA
at $V_R = 25\text{ V}, T_J = 150\text{ }^\circ\text{C}$		100	μA
Diode Capacitance	C_d	2	pF
Reverse Recovery Time	t_{rr}	4	ns
at $I_F = I_R = 10\text{ mA}$ to $I_R = 1\text{ mA}$, $R_L = 100\ \Omega$			

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121606007
 ISO 9001 : 2008 Certificate No. 50114012
 OHSAS 18001 : 2007 Certificate No. 05131508006
 IECQ QC 080000 Certificate No. E0241002014102

Dated : 15/06/2012

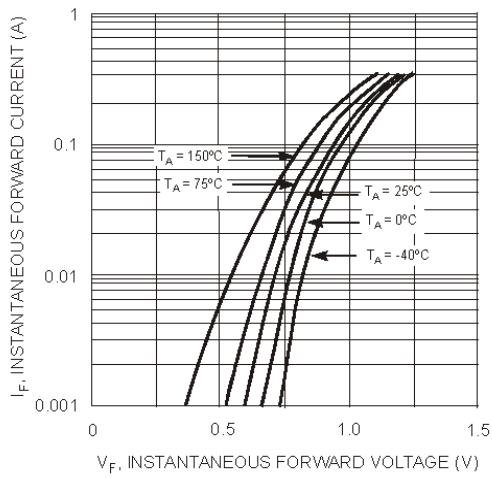


Fig. 1 Forward Characteristics

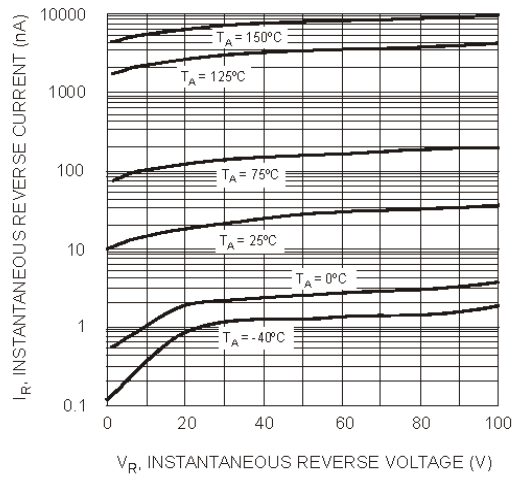


Fig. 2 Typical Reverse Characteristics

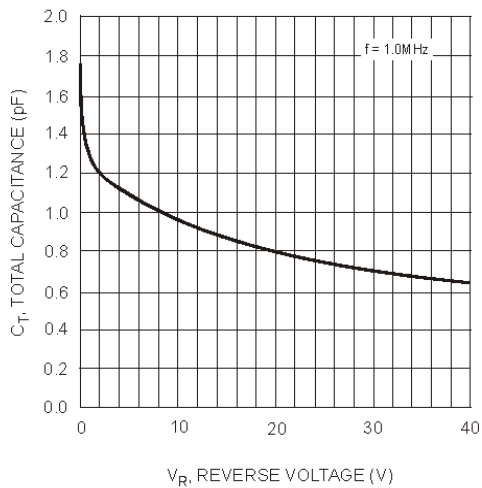


Fig. 3 Typical Capacitance vs. Reverse Voltage

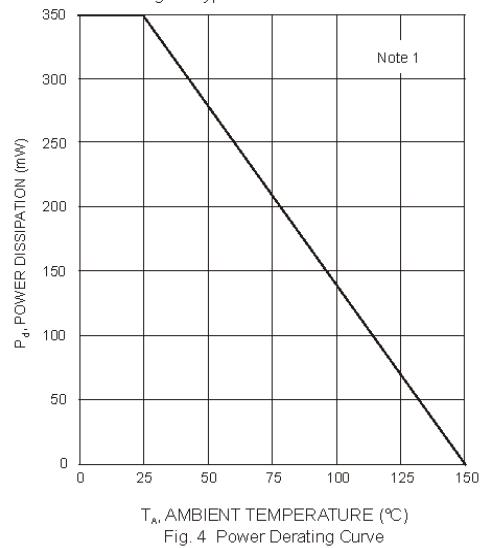


Fig. 4 Power Derating Curve